

TOSHIBA

U2FWJ44M

TOSHIBA SCHOTTKY BARRIER RECTIFIER SCHOTTKY BARRIER TYPE

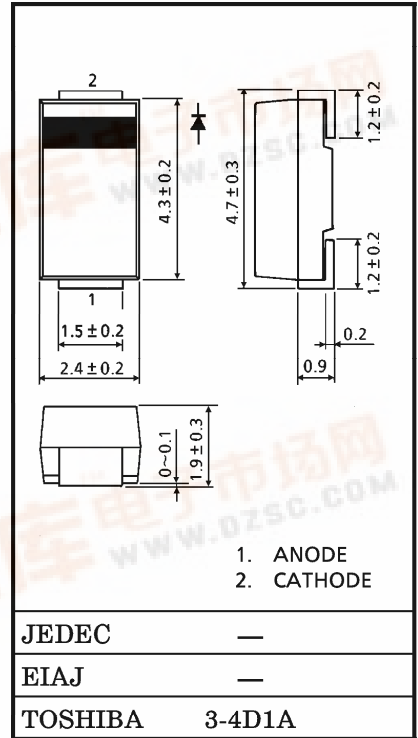
U2FWJ44M

SWITCHING TYPE POWER SUPPLY APPLICATION

Unit in mm

PORTABLE EQUIPMENT BATTERY APPLICATION

- Low Forward Voltage : $V_{FM} = 0.45 \text{ V (Max.)}$
- Average Forward Current : $I_F (AV) = 2.0 \text{ A}$
- Repetitive Peak Reverse Voltage : $V_{RRM} = 30 \text{ V}$
- Surface Mounting Plastic Mold Package



MAXIMUM RATINGS

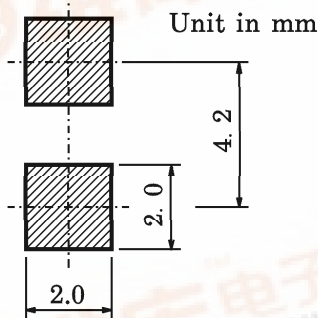
CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Average Forward Current	$I_F (AV)$	2.0	A
Peak One Cycle Surge Forward Current (Non-Repetitive)	I_{FSM}	60 (50Hz)	A
Junction Temperature	T_j	-40~125	°C
Storage Temperature Range	T_{stg}	-40~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

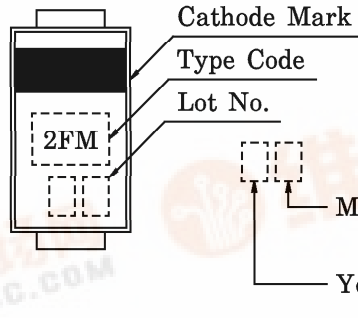
Weight : 0.06 g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V_{FM}	$I_{FM} = 2.0 \text{ A}$	—	—	0.45	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 30 \text{ V}$	—	—	500	μA
Junction Capacitance	C_j	$V_R = 10 \text{ V}, f = 1.0 \text{ MHz}$	—	125	—	pF
Thermal Resistance (Junction to Ambient)	$r_{th (j-a)}$	On ceramic substrate	—	—	60	°C/W
		On glass-epoxy substrate	—	—	145	

Standard Soldering Pad



MARKING



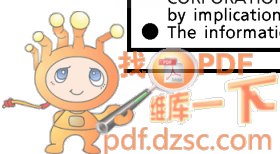
Code	Type
2FM	U2FWJ44M

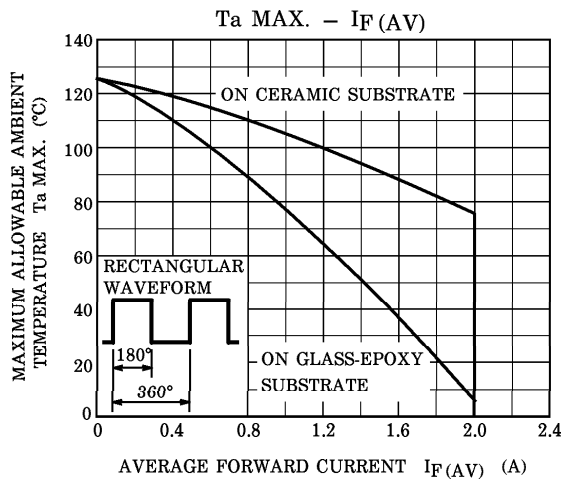
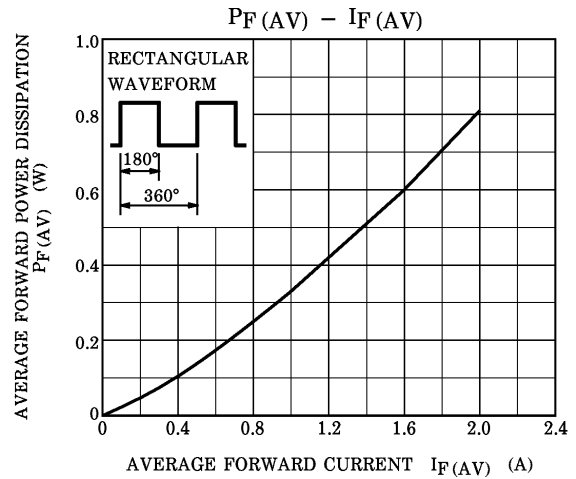
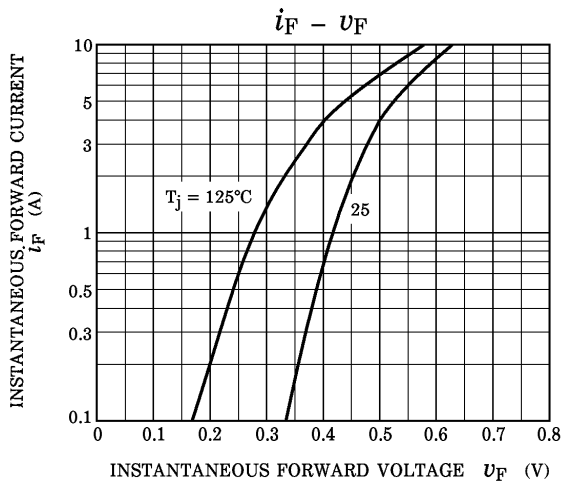
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	ON CERAMIC SUBSTRATE	ON GLASS-EPOXY SUBSTRATE
Soldering land : a	2 mm × 2 mm	6 mm × 6 mm
Substrate size : b	50 mm × 50 mm	50 mm × 50 mm
Substrate thickness : c	0.64 mm	1.6 mm

